Ultrafast Electrochemical Synthesis of Defect-Free In₂Se₃ Flakes for Large-Area Optoelectronics

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Abstract

Indium(III) selenide (In₂Se₃), an important semiconductor, has been applied in various electronics and optoelectronics owing to its thickness-dependent direct bandgap (1.3-2.8 eV) and exceptional optoelectronic properties and high stability [1]. However, the scalable production of defect-free In₂Se₃ flakes with large crystal domains remains an impediment to their practical applications. Here, a facile electrochemical strategy is presented for the ultrafast delamination (30 min) of bulk layered In₂Se₃ crystals in dimethylformamide (DMF) containing (tetrahexylammonium(THA⁺), resulting in high-yield (83%) production of In₂Se₃ flakes with large lateral size (up to 26 µm). The intercalation of THA⁺ ions mainly creates stage-3 intercalated compounds in which every three layers of In₂Se₃ are occupied by one layer of THA molecules [2]. The subsequent exfoliation leads to a majority of trilayer In₂Se₃ nanosheets (4 nm). Owing to the excellent solution processability of exfoliated sheets (2 mg/mL in DMF), large-area (400 μ m \times 20 μ m) photodetectors are fabricated based on filtrated In₂Se₃ thin films from their stable dispersions. The fabricated devices demonstrated high responsivity (≈1 mA W⁻¹), superfast rise (41 ms) and decay time (39 ms) and high stability to light, superior to the performances of other 2D materials such as, graphene, black phosphorus, MoS_2 , and $WS_2[3]$.

References

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Figure

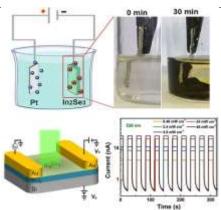


Figure 1: Schematic illustration and photographs of the electrochemical delamination of bulk In₂Se₃ (top) and schematic and photoresponse of the In₂Se₃-based thin film photodetector(down).